CLAIMS:

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- 1. A method for processing a substrate, comprising:
- a) positioning a substrate having a first conductive material disposed thereon in a processing chamber containing an electrochemical bath;
- b) depositing a second conductive material on the first conductive material as the conductive material is contacted with the electrochemical bath by applying a plating bias to the substrate while immersing the substrate into the electrochemical bath; and
- depositing a third conductive material in situ on the second conductive material by an electrochemical deposition technique to fill the feature.
- 2. The method of claim 1, wherein applying the bias to the substrate comprises applying a voltage of between about 0.8 volts and about 20 volts.
- The method of claim 1, wherein the bias is applied for a period of time between about 0.1 seconds and about 4 seconds.
- 4. The method of claim 1, wherein applying the bias to the substrate comprises applying a voltage of between about 5 volts and about 20 volts for a period of time between about 0.5 seconds and about 2 seconds.
- The method of claim 1, wherein electrochemical deposition technique comprises a pulse plating technique.
- 6. The method of claim 1, wherein applying the bias to the substrate comprises exposing the substrate to a charge density between about 20 mA*sec/cm² and about 160 mA*sec/cm².
- The method of claim 1, wherein the first, second, and third conductive materials
 are selected from the group of copper, doped copper, copper alloys, and combinations
 thereof.
- 8. A method for electrochemically depositing a conductive material into a high

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aspect ratio structure on a substrate, comprising:

- a) depositing a seed layer in the high aspect ratio structure on the substrate:
- b) applying a plating bias over the substrate by exposing the substrate to a charge density between about 20 mA*sec/cm² and about 160 mA*sec/cm² while immersing the substrate into an electrochemical bath to deposit a patching layer in the high aspect ratio structure; and
- c) depositing a conductive material on the patching layer in situ to fill the high aspect ratio structure.
- The method of claim 8, wherein the charge density comprises applying a voltage
 of between about 0.8 volts and about 20 volts for a period of time between about 0.1
 seconds and about 4 seconds.
- 10. The method of claim 8, wherein the seed layer, the patching layer, and the conductive materials are selected from the group of copper, doped copper, copper alloys, and combinations thereof.
- 11. A method for filling a high aspect ratio structure on a substrate in an electrochemical bath, comprising:
- a) providing a substrate having discontinuous conductive layers formed thereon;
- b) reducing the formation of discontinuous conductive layers and minimizing agglomeration of subsequently deposited conductive material while immersing the substrate into the electrochemical bath; and
 - c) filling the high aspect ratio structure with a conducive material.
- 12. The method of claim 11, wherein the reduction of the formation of discontinuous conductive layers and minimizing agglomeration of subsequently deposited conductive material comprises applying a plating bias to the substrate while immersing the substrate into an electrochemical bath.
- 13. The method of claim 12, wherein applying the bias to the substrate comprises applying a voltage of between about 0.8 volts and about 20 volts.

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- 14. The method of claim 12, wherein the bias is applied for a period of time between about 0.1 seconds and about 4 seconds.
- 15. The method of claim 12, wherein applying the bias to the substrate comprises applying a voltage of between about 5 volts and about 20 volts for a period of time between about 0.5 seconds and about 2 seconds.
- 16. The method of claim 12, wherein filling the high aspect ratio structure with a conducive material comprises a pulse plating technique.
- 17. The method of claim 16, wherein the electrochemical deposition technique comprises a pulse plating technique.
- 18. The method of claim 12, wherein applying the bias to the substrate comprises exposing the substrate to a charge density between about 20 mA*sec/cm² and about 160 mA*sec/cm².
- 19. The method of claim 18, wherein the charge density is selected based upon the amount of material to be deposited.
- 20. The method of claim 1, wherein the charge density is selected based upon the amount of second conductive material to be deposited.
- The method of claim 8, wherein the charge density is selected based upon the amount of patching layer material to be deposited.